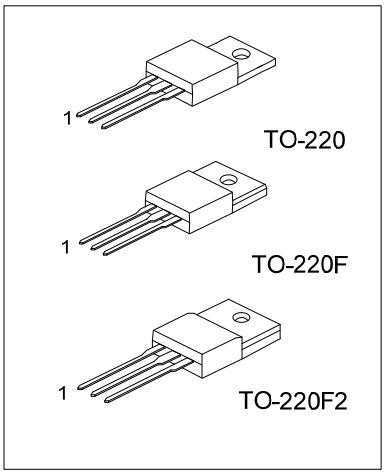
2SC5027E

NPN SILICON TRANSISTOR

HIGH VOLTAGE AND HIGH RELIABILITY TRANSISTOR

.



■ FEATURES

* High Speed Switching
* Wide SOA

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC5027EL-x-TA3-T	2SC5027EL-x-TA3-T	TO-220	B	C	E	Tube
2SC5027EL-x-TF2-T	2SC5027EL-x-TF2-T	TO-220F2	B	C	E	Tube
2SC5027EL-x-TF3-T	2SC5027EL-x-TF3-T	TO-220F	B	C	E	Tube

2SC5027EL-x-TA3-T (1)Packing Type (2)Package Type (3)Rank (4)Lead Plating	(1) T: Tube (2) TA3: TO-220, TF3: TO-220F (3) x: refer to Classification of h_{FE1} (4) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUATE MAXIUM RATINGS (T_C = 25℃)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	750	V
Collector-Emitter Voltage		V_{CEO}	700	V
Collector-Emitter Voltage		V_{EBO}	7	V
Peak Collector Current		I_C	3	A
Collector Current (Pulse)		I_{CP}	10	A
Base Current		I_B	1.5	A
Power Dissipation	TO-220/TO-220F	P_D	50	W
	TO-220F2		52	
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-40 ~ +150	℃

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C= 25℃, unless otherwise specified.)

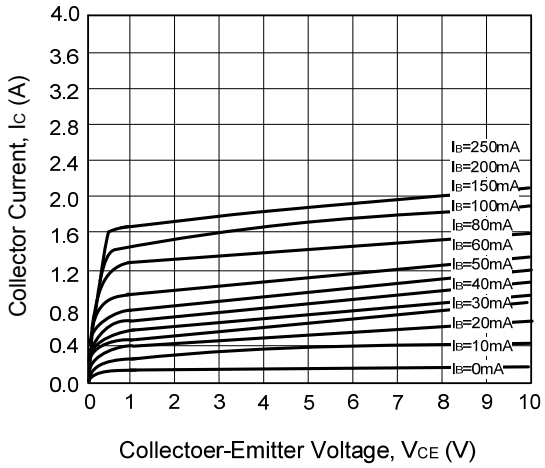
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA, I_E=0	750			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=5mA, I_B=0	700			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA, I_C=0	7			V
Collector-Emitter sustaining Voltage	$V_{CEO(SUS)}$	I_C=1.5A, I_{B1}= -I_{B2}=0.3A L=2mH, Clamped	700			V
Collector Cut-off Current	I_{CBO}	V_{CB}=750V, I_E=0			10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	h_{FE1}	V_{CE}=5V, I_C=0.2A	10		40	
	$h_{FE\,2}$	V_{CE}=5V, I_C=1A	8			
Collector-Emitter Saturation Voltage	$V_{CE\,(SAT)}$	I_C=1.5A, I_B=0.3A			2	V
Base-Emitter Saturation Voltage	$V_{BE\,(SAT)}$	I_C=1.5A, I_B=0.3A			1.5	V
Output Capacitance	C_{OB}	V_{CB}=10V, f=1MHz, I_E=0		60		pF
Current Gain Bandwidth Product	f_T	V_{CE}=10V, I_C=0.2A		15		MHz
Turn ON Time	t_{ON}	V_{CC}=400V			0.5	μs
Storage Time	t_S	I_C=5I_{B1}= -2.5I_{B2}=2A			3	μs
Fall Time	t_F	R_L=200Ω			0.3	μs

■ CLASSIFICATION of h_{FE1}

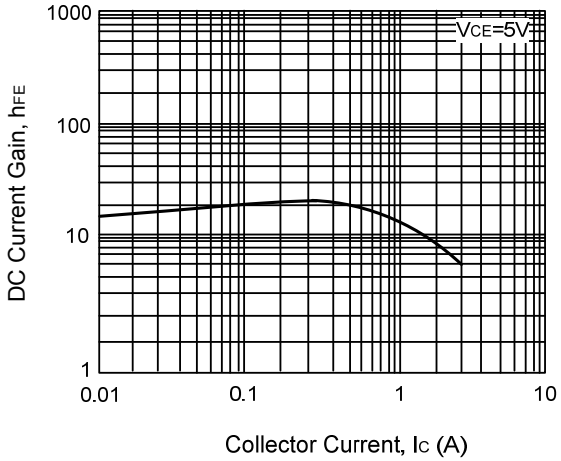
CLASSIFICATION	N	R	O
RANGE	10 ~ 20	15 ~ 30	20 ~ 40

■ TYPICAL CHARACTERISTICS

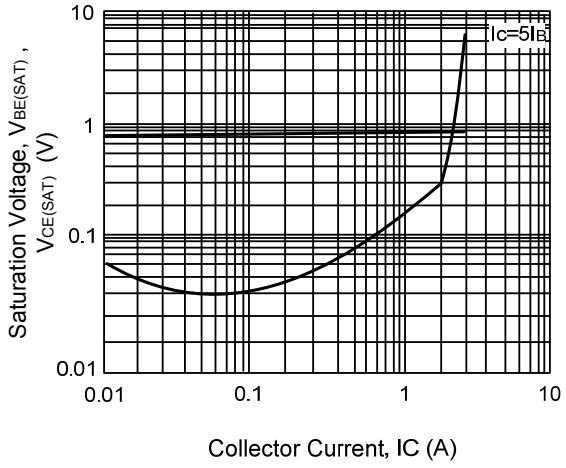
Static Characteristic



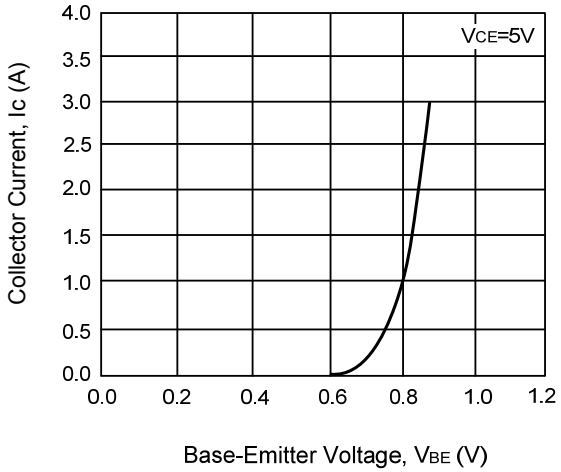
DC Current Gain



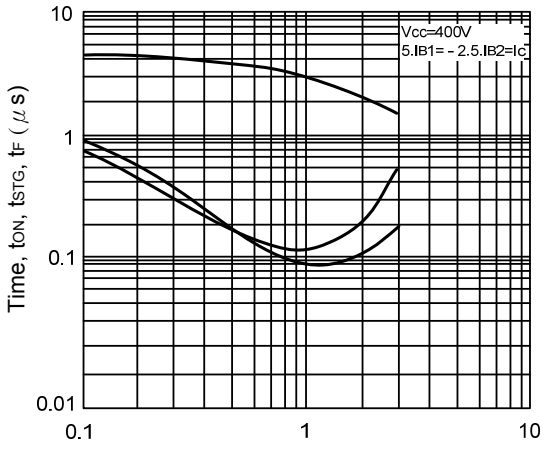
Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



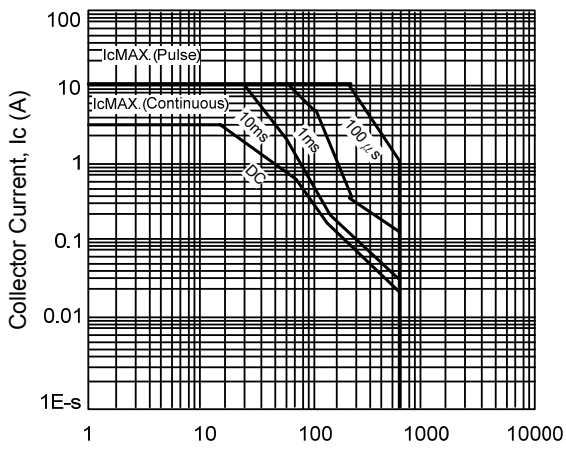
Base-Emitter on Voltage



Switching Time

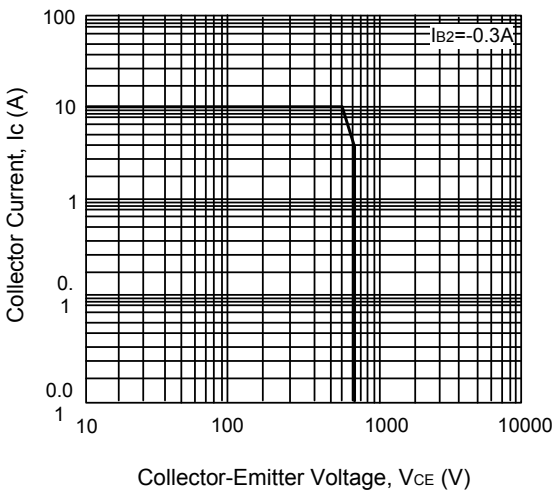


Safe Operating Area



■ TYPICAL CHARACTERISTICS(Cont.)

Reverse Operating Area



Power Derating